[PHOTOLITHOGRAPHY PROCESS WITH HYBRID CHROMELESS PAHSE SHIFT MASK]

Abstract of Disclosure

The present invention relates to a photolithography process using hybrid chromeless phase shift masks. A mask having a gate pattern formed on a base plate is provided. A 180-degree shifter layer is formed at critical dimension locations of the base plate. The mask of the present invention can be used for transferring the gate pattern to a photoresist layer in the exposure process.

Figures